

IN THE ABSTRACT:

Amend the Abstract as follows:

A high frequency semiconductor device ~~includes~~ including wiring layers which are formed above a semiconductor substrate and in which transmission lines are formed by combining with a ground plate having a potential fixed at the ground potential, at least one crossing portion in which the wiring layers mutually cross, with insulating interlayers provided therebetween, and at least one separation electrode being selectively provided on one of the insulating interlayers, the at least one separation electrode having a potential fixed at the ground potential. Accordingly, in the high frequency semiconductor device, ~~the~~ electrical interference between two crossing wiring layers is prevented and transmission loss is suppressed.

ABSTRACT OF THE DISCLOSURE:

A high frequency semiconductor device including wiring layers which are formed above a semiconductor substrate and in which transmission lines are formed by combining with a ground plate having a potential fixed at the ground potential, at least one crossing portion in which the wiring layers mutually cross, with insulating interlayers provided therebetween, and at least one separation electrode being selectively provided on one of the insulating interlayers, the at least one separation electrode having a potential fixed at the ground potential. Accordingly, in the high frequency semiconductor device, electrical interference between two crossing wiring layers is prevented and transmission loss is suppressed.